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Supporting Information

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An Instant Change of Elastic Lattice Strain during Cu₂Se Phase Transition: Origin of Abnormal Thermoelectric Properties

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An instant change of elastic lattice strain during Cu₂Se phase transition: origin of abnormal thermoelectric properties

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Figure S1. Characterization of Cu_2Se sample structure. TEM images (a-c) on both sides of the Cu_2Se grain boundary (yellow dashed line) under different magnifications. Selected area electron diffraction of the red area (d) and the blue area (e) in (a). Comparison of differences in the two diffractions in (f).



Figure S2. Structual relationships in Cu₂Se before and after phase transformation. Selected area electron diffraction (a, d, g), simulated electron diffraction (b, e, h), and structural schematic diagrams (c,e,i) of α -phase Cu₂Se along [0-10], [10-1] and β -phase Cu₂Se along [110] directions are compared, respectively.



Figure S3. The Cu₂Se structure is stable at 388 K for a long time. (a,d) Low magnification TEM images at 0 min and 68 min. (b,e) Electron diffraction from the A crystal grains. (c,f) Electron diffraction from the B crystal grains.



Figure S4. Contrast in the diffraction patterns of the α -Cu₂Se [10-1] domain, α -Cu₂Se [0-10] domain, and β -Cu₂Se [110].



Figure S5. Dislocation changes in Cu₂Se upon *in-situ* heating at different temperatures. The temperatures are (a) RT, (b) 373 K, (c) 378 K, (d) 383 K (e) 388 K, and (f) 393 K.



Figure S6. Low-magnification TEM images of Cu₂Se during the *in-situ* **heat-induced phase transformation at different temperatures.** The temperatures are (a) RT, (b) 383 K, (c) 388 K and (d) 393 K.



Figure S7. Thermoelectric properties of Cu₂Se as a function of temperature: (a) resistivity, (b) carrier concentration ($p_{\rm H}$) and carrier mobility (μ).

B. Videos

Video S1. *In-situ* TEM of the Cu₂Se phase transformation by rising temperature from room temperature to ~120°C (×5 times faster than the real speed).

Video S2. *In-situ* selected area electron diffraction (SAED) patterns from α -Cu₂Se [1-21] domain to β -Cu₂Se [112], when the temparatur is raised from 100 to 150°C

(×5 times faster than the real speed).

Video S3. *In-situ* SAED patterns from β -Cu₂Se [112] to α -Cu₂Se [100] domain, when the temparatur is decreased from 150 to 100°C (×5 times faster than the real speed).

Video S4. *In-situ* SAED patterns from α -Cu₂Se [100] domain to β -Cu₂Se [112], when the temparatur is raised from 100 to 150°C (×5 times faster than the real speed).

Video S5. *In-situ* SAED patterns from β -Cu₂Se [112] to α -Cu₂Se [1-21] domain, when the temparatur is decreased from 150 to 100°C (×5 times faster than the real speed).

Video S6. *In-situ* high resolution STEM of the the Cu₂Se phase transformation, when the temparatur is cycled back and forth among 110 to 115° C.